

## N-Channel MOSFET

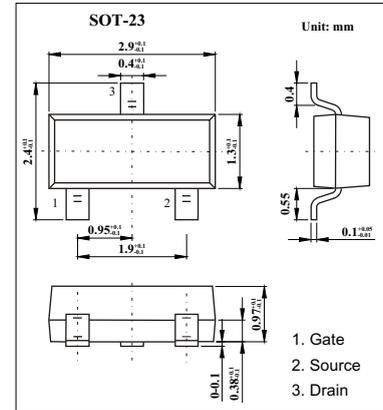
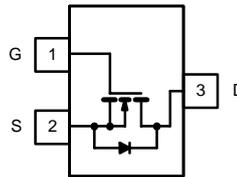
### KI2302DS

#### Features

$V_{DS}=20V$

$R_{DS(on)}=0.085$  @ $V_{GS}=4.5V$ ,  $I_D=3.6A$

$R_{DS(on)}=0.115$  @ $V_{GS}=2.5V$ ,  $I_D=3.1A$



#### Absolute Maximum Ratings $T_a = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current	$I_D$	$T_a = 25$	A
		$T_a = 70$	
Pulsed Drain Current	$I_{DM}$	10	
Power Dissipation	$P_D$	$T_a = 25$	W
		$T_a = 70$	
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	178	/W
Junction Temperature	$T_J$	150	
Storage Temperature	$T_{stg}$	-55 to 150	

## KI2302DS

Electrical Characteristics Ta = 25

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 10 μA	20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.62	0.95	1.9	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55			10	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V			± 100	nA
Drain-Source On-Resistance *	r <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.6 A		0.045	0.085	
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3.1 A		0.070	0.115	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 4.5 V	6			A
		V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 2.5 V	4			
Forward Transconductance *	g <sub>fs</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 3.6 A		8		S
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		300		pF
Output Capacitance	C <sub>oss</sub>			120		
Reverse Transfer Capacitance	C <sub>rss</sub>			80		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.6A		4.0	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.65		
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =5.5 Ω, I <sub>D</sub> ≅3.6A, V <sub>GEN</sub> =4.5V, R <sub>G</sub> =6Ω		7	15	ns
Rise Time	t <sub>r</sub>			55	80	
Turn-Off Delay Time	t <sub>d(off)</sub>			16	60	
Fall-Time	t <sub>f</sub>			10	25	
Continuous Source Current (Diode Conduction)	I <sub>S</sub>			0.94		A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.94A, V <sub>GS</sub> = 0 V		0.76	1.2	V

\*Pulse test: PW 300 μs duty cycle 2%..

## ■ Marking

Marking	A2SHB
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